ABSTRACT OF THE DISCLOSURE

Disclosed herein is a method of manufacturing a nitride semiconductor light emitting device. a nitride semiconductor crystal film is grown on a substrate. The nitride semiconductor crystal film has a composition represented as $Al_xIn_yGa_{(1-x-y)}N$ ($0 \leq x \leq 1$, $0 \leq y \leq 1$, $0 \leq x+y \leq 1$). After that, in order to remove an oxide film naturally formed on the nitride semiconductor crystal film, a surface treatment process is performed on the nitride semiconductor crystal film by making use of hydrogen gas or mixed gases containing hydrogen. Subsequently, on the nitride semiconductor crystal film there are successively formed a first conductive nitride semiconductor layer, an active layer, and a second conductive nitride semiconductor layer.